

Single N Channel MOSFET

Features

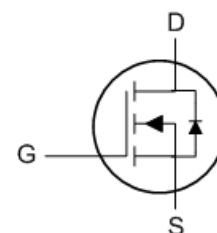
- ★ Advanced Trench MOS Technology
- ★ 100% EAS Guaranteed
- ★ Fast Switching Speed
- ★ Green Device Available

Applications

- ★ Power Tools.
- ★ Motor Control.
- ★ UPS
- ★ Synchronous Rectification in SMPS



TO220 Pin Configuration



Product Summary

BVDSS	RDSON	ID
100V	2.2mΩ	308A

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current ^{1,6}	308	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current ^{1,6}	218	A
I_{DM}	Pulsed Drain Current ²	550	A
EAS	Single Pulse Avalanche Energy ³	1012.5	mJ
I_{AS}	Avalanche Current	45	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation ⁴	429	W
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 175	$^\circ\text{C}$

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	60	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	0.35	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	100	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=30A$	---	1.8	2.2	m Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	2	---	4	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=80V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=80V$, $V_{GS}=0V$, $T_J=100^\circ\text{C}$	---	---	100	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V$, $I_D=20A$	---	75	---	S
Q_g	Total Gate Charge	$V_{DS}=50V$, $V_{GS}=10V$, $I_D=20A$	---	200	---	nC
Q_{gs}	Gate-Source Charge		---	53.3	---	
Q_{gd}	Gate-Drain Charge		---	49	---	
$T_d(on)$	Turn-On Delay Time	$V_{DD}=50V$, $V_{GS}=10V$, $R_G=3\Omega$, $I_D=20A$	---	47	---	ns
T_r	Rise Time		---	28	---	
$T_d(off)$	Turn-Off Delay Time		---	79	---	
T_f	Fall Time		---	18	---	
C_{iss}	Input Capacitance	$V_{DS}=50V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	13362	---	pF
C_{oss}	Output Capacitance		---	1917	---	
C_{rss}	Reverse Transfer Capacitance		---	387	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5,6}	$V_G=V_D=0V$, Force Current	---	---	80	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=1A$, $T_J=25^\circ\text{C}$	---	---	1.1	V
t_{rr}	Reverse Recovery Time	$I_F=20A$, $di/dt=100A/\mu s$, $T_J=25^\circ\text{C}$	---	70	---	nS
Q_{rr}	Reverse Recovery Charge		---	580	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=50V$, $V_{GS}=10V$, $L=1.0mH$, $I_{AS}=45A$
- 4.The power dissipation is limited by 175°C junction temperature.
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.
- 6.Bonding wire limitation current is 120A.

Typical Characteristics

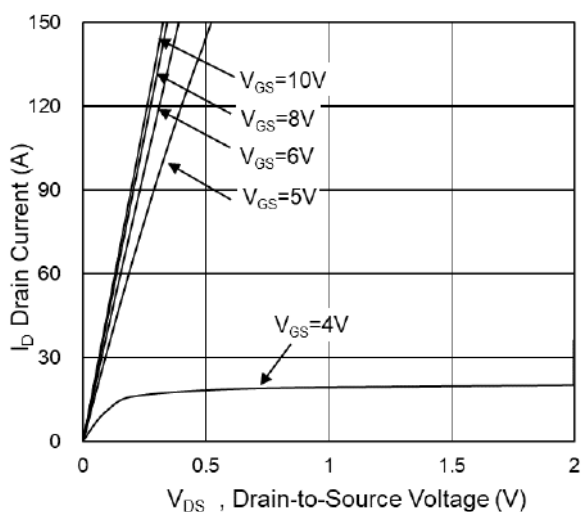


Fig.1 Typical Output Characteristics

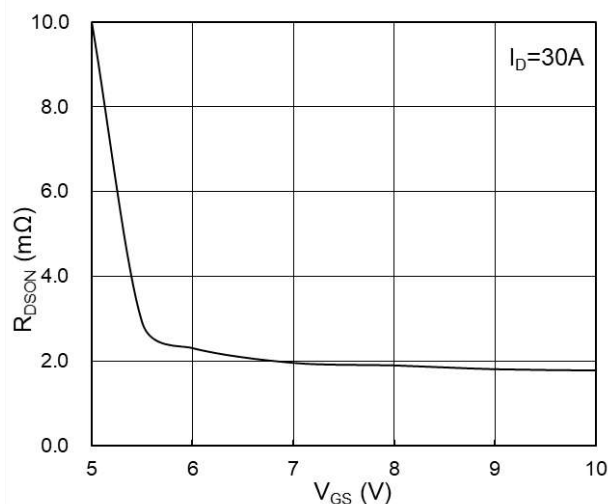


Fig.2 On-Resistance vs G-S Voltage

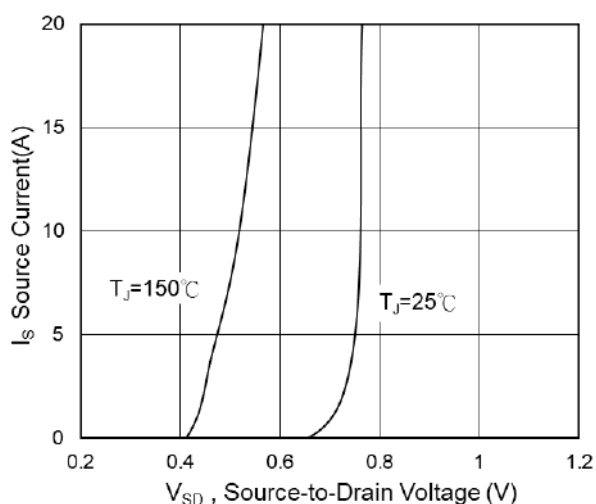


Fig.3 Source-Drain Forward Characteristics

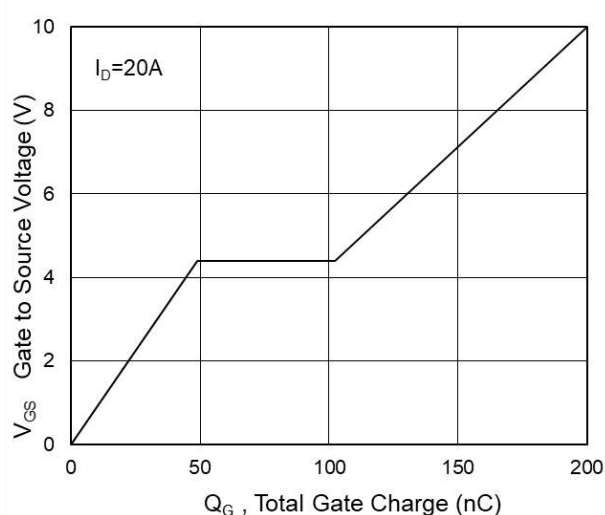


Fig.4 Gate-Charge Characteristics

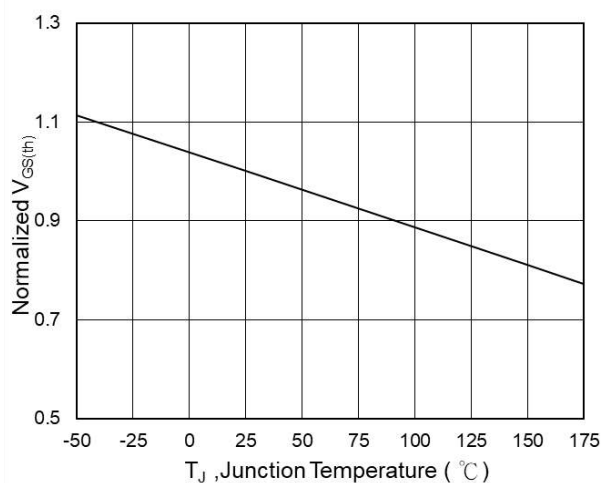


Fig.5 Normalized $V_{GS(th)}$ vs T_J

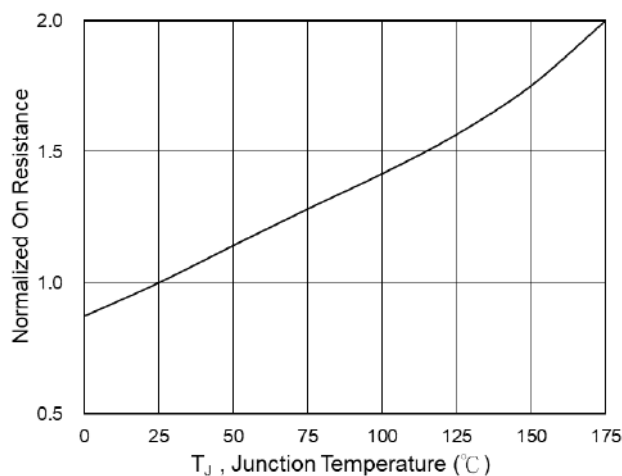


Fig.6 Normalized $R_{DS(on)}$ vs T_J

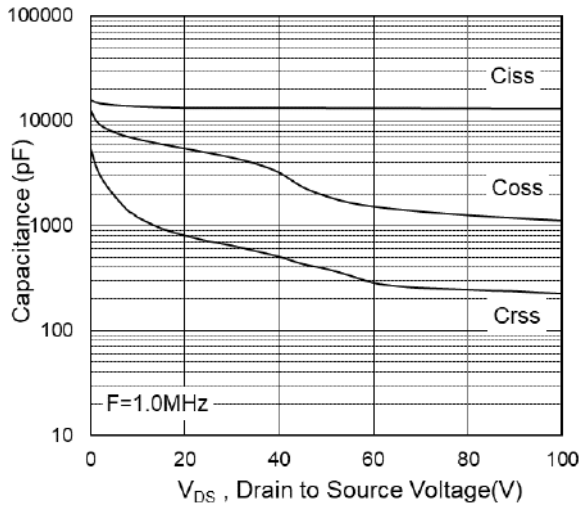


Fig.7 Capacitance

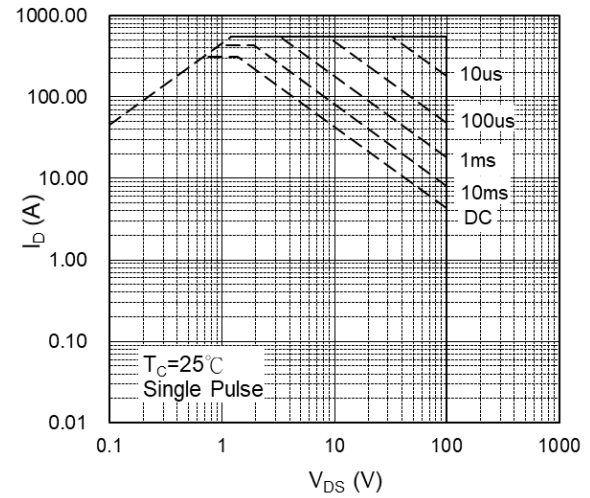


Fig.8 Safe Operating Area

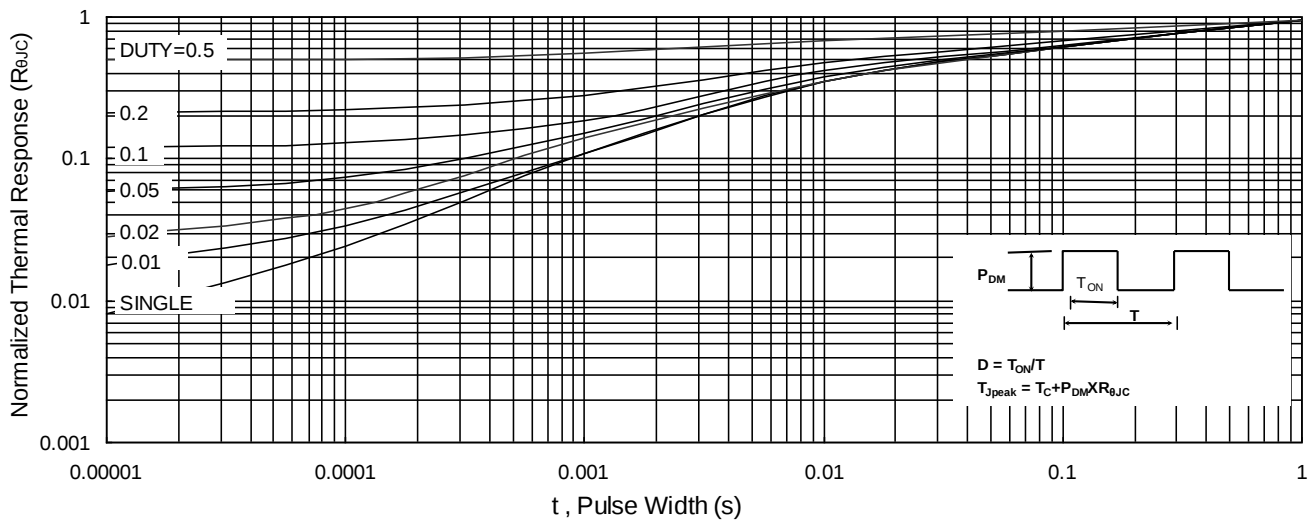


Fig.9 Normalized Maximum Transient Thermal Impedance

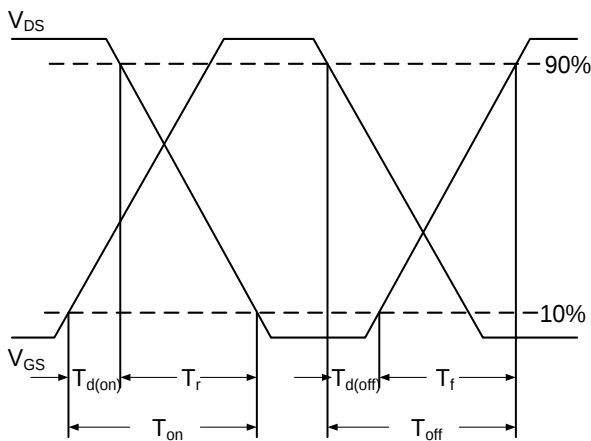


Fig.10 Switching Time Waveform

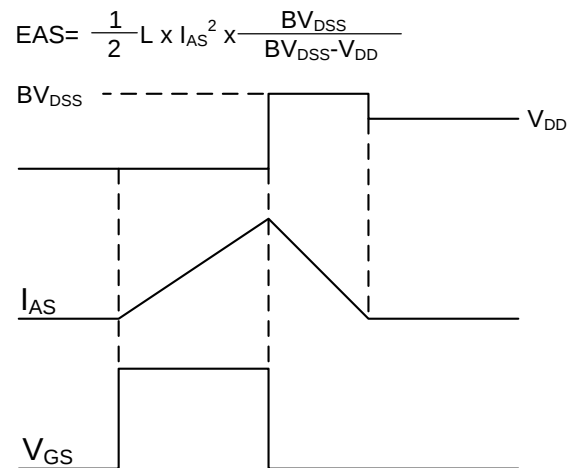


Fig.11 Unclamped Inductive Switching Waveform